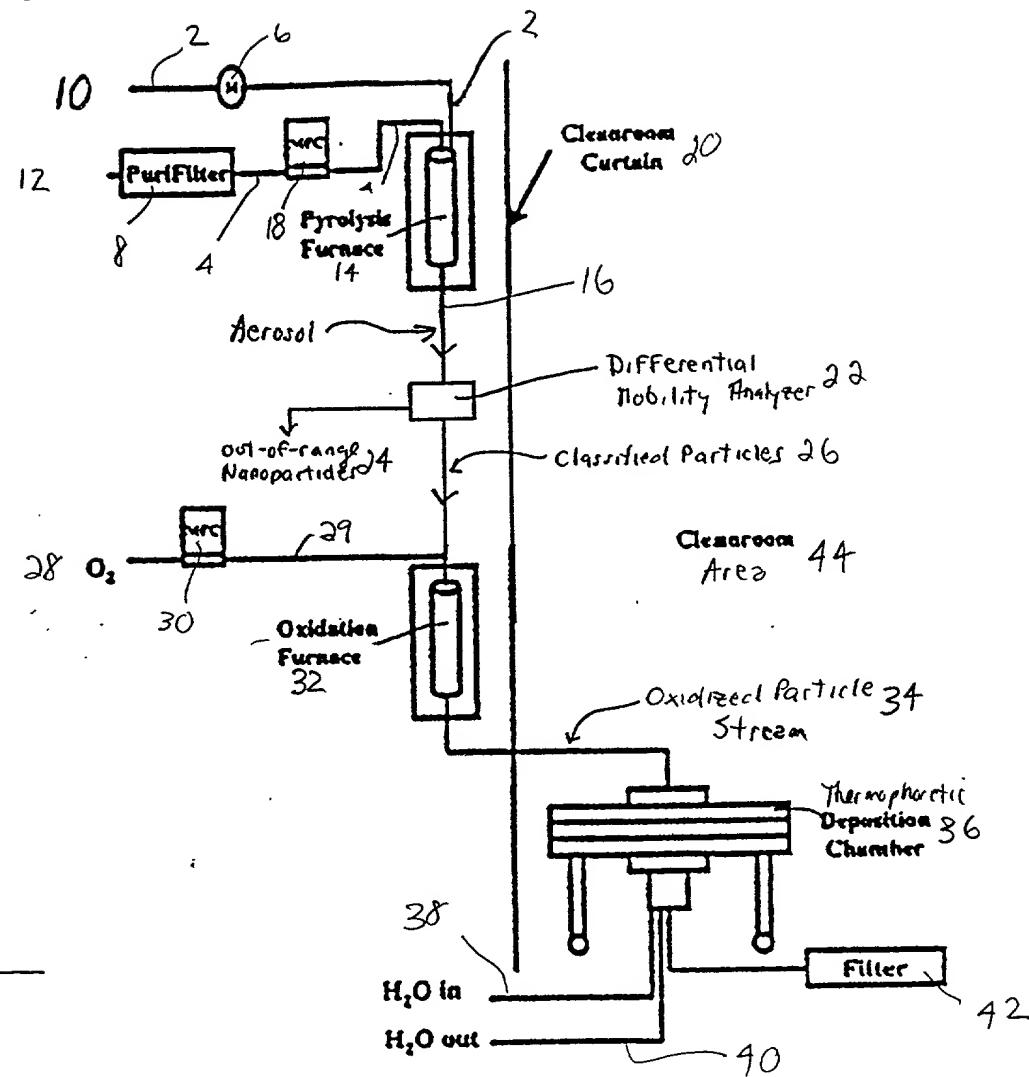


FIGURE 1

FIGURE 2



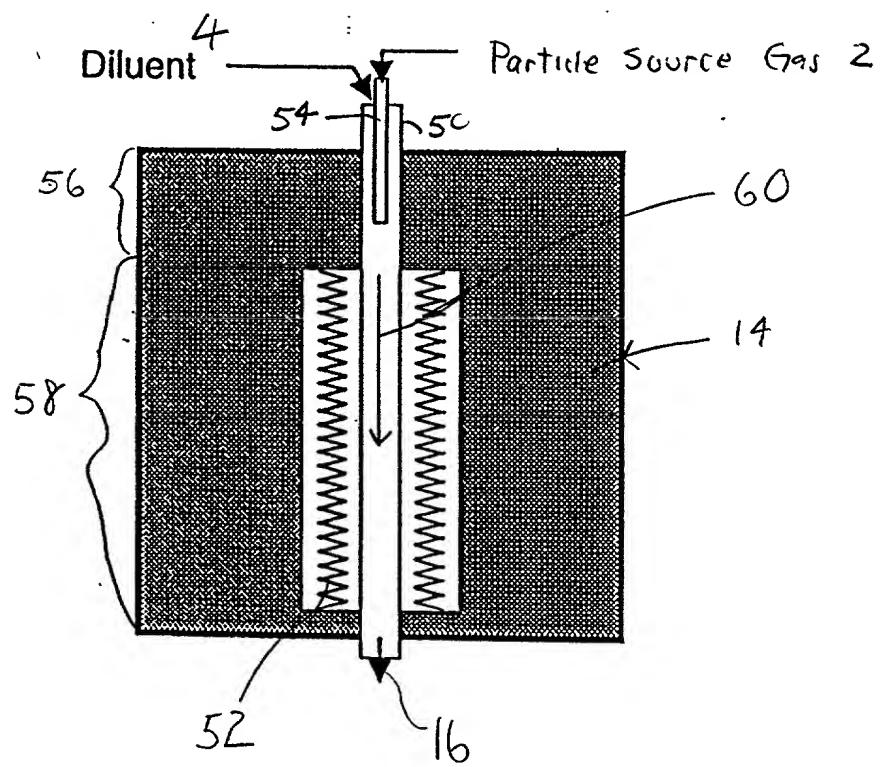


FIGURE 3

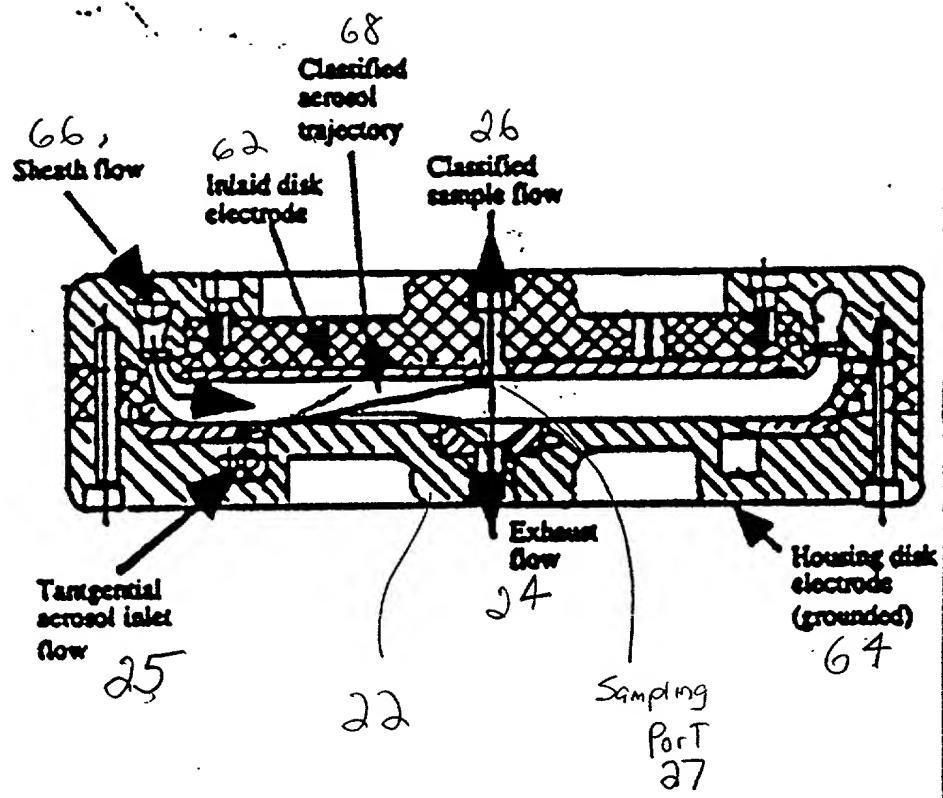


FIGURE 4

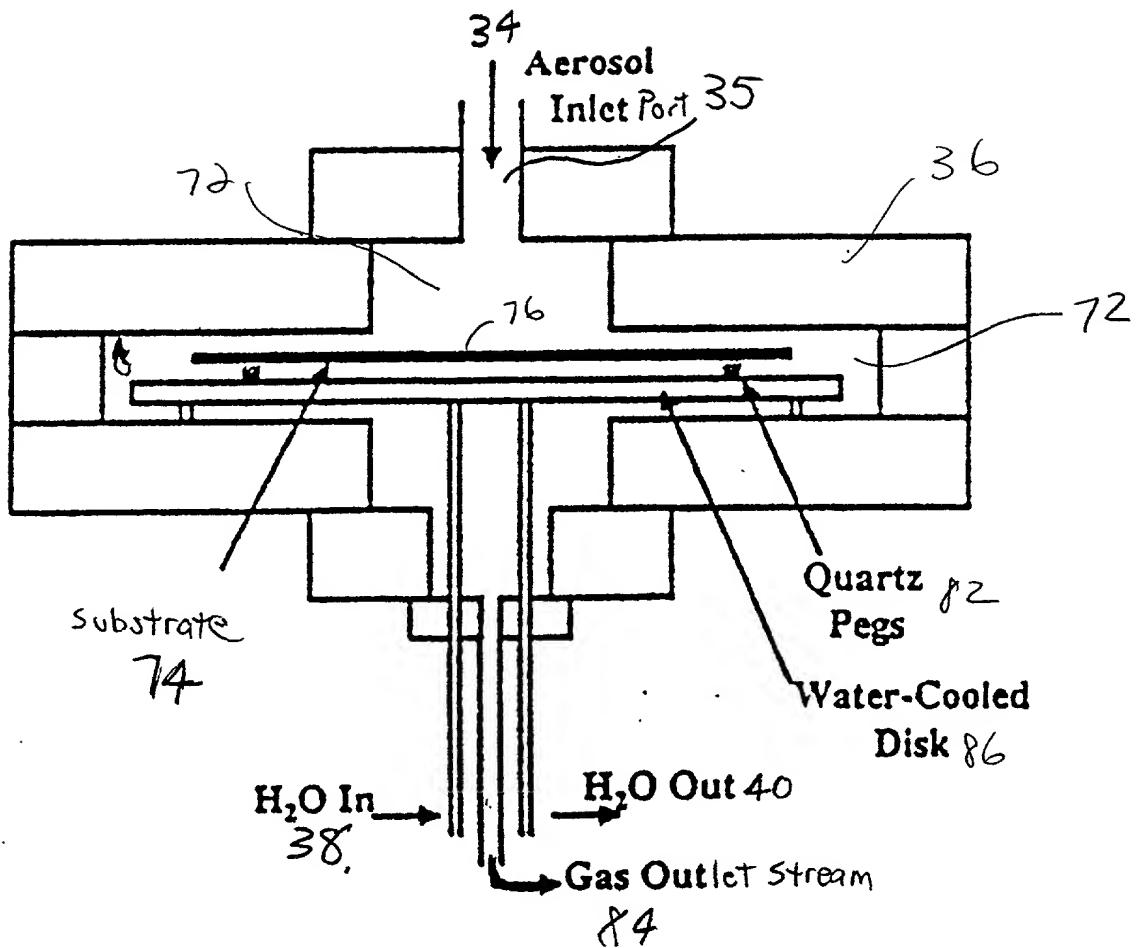


FIGURE 5

FIGURE 6

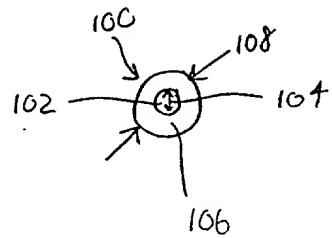


FIGURE 7

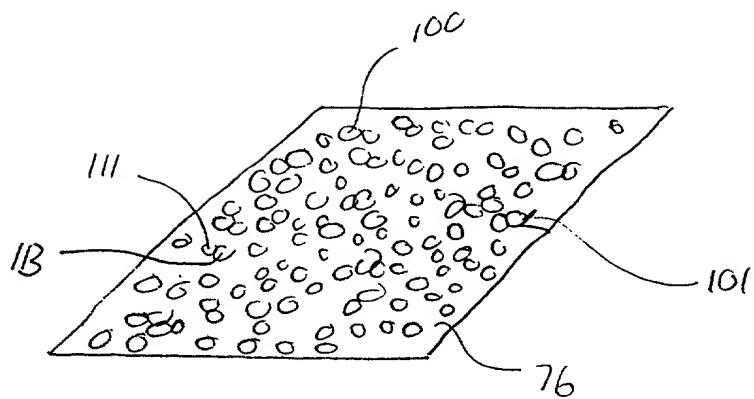


FIGURE 8

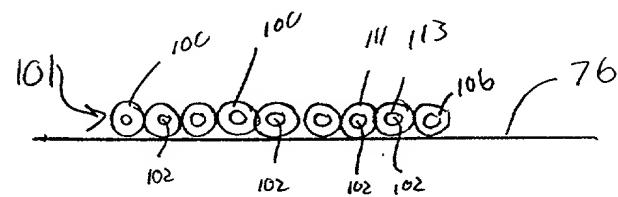


FIGURE 10

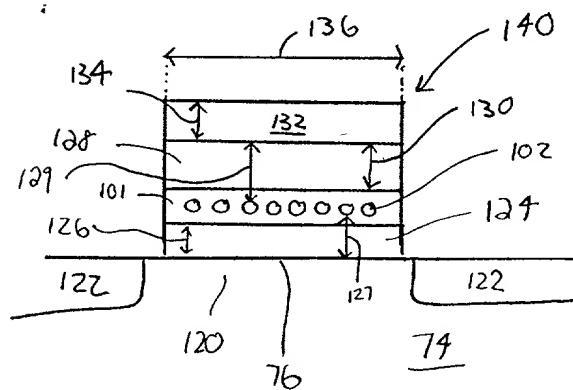


FIGURE 9

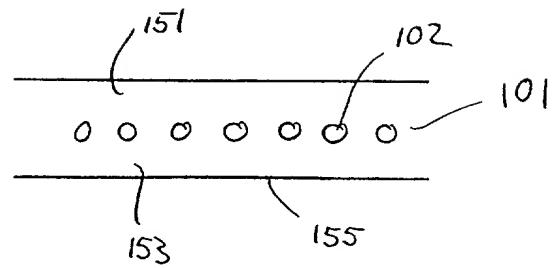
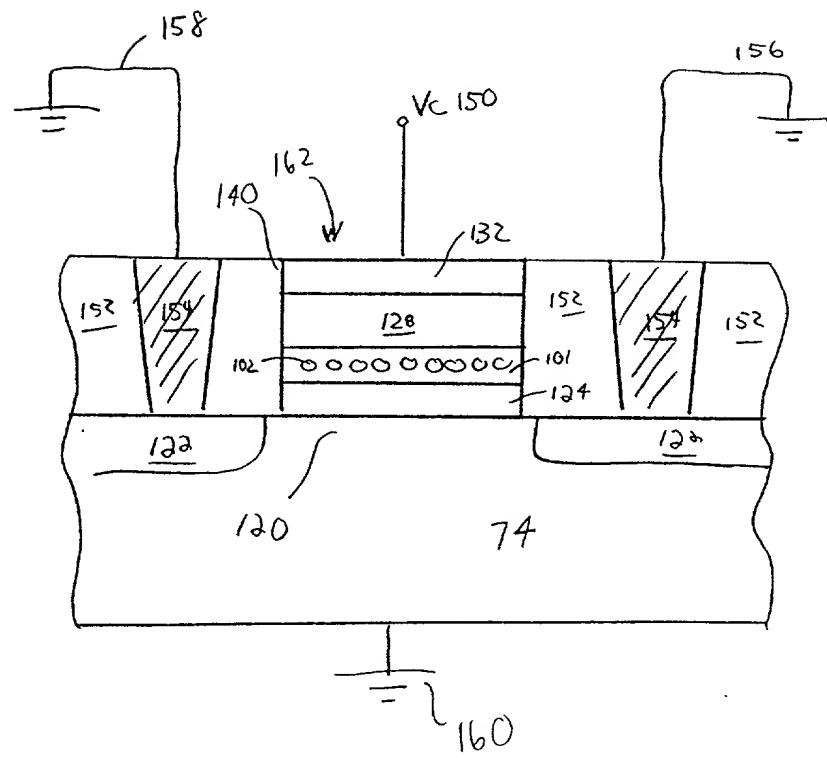


FIGURE 11



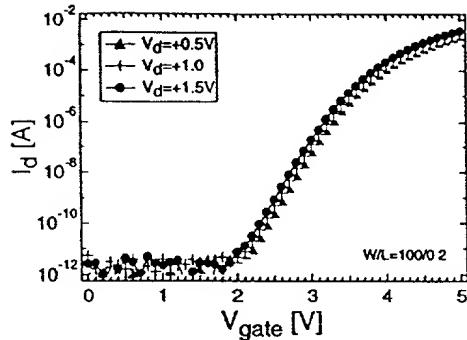


FIG 12 Subthreshold characteristics of a $0.2\mu\text{m}$ n-type aerosol-nanocrystal floating-gate MOSFET (subthreshold slope = 200mV/dec ; DIBL = 100mV/V).

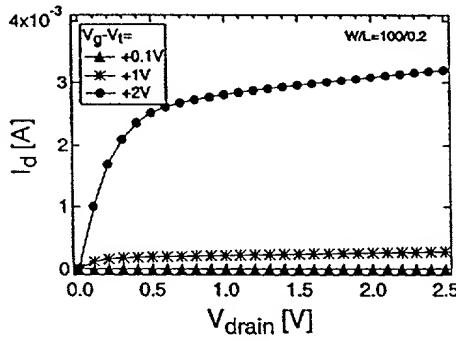


FIG 13 Output characteristics of a $0.2\mu\text{m}$ aerosol-nanocrystal floating-gate MOSFET; drive current = $30\mu\text{A}/\mu\text{m}$.

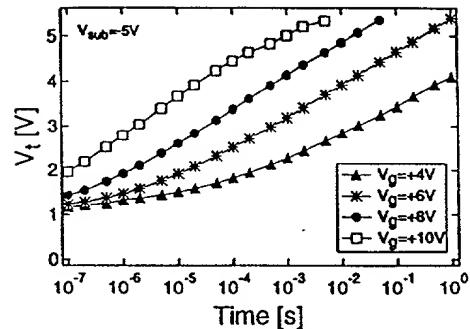


FIG 14 Programming transients (uniform FN tunneling) of the nanocrystal NVM device.

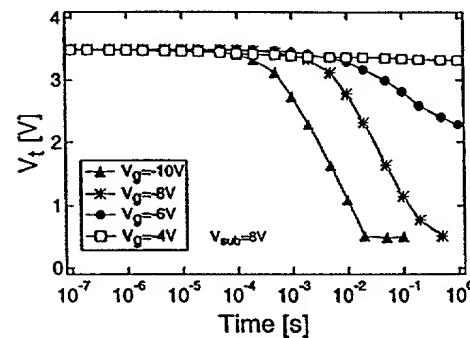


FIG 15 Erase transients (uniform FN tunneling).

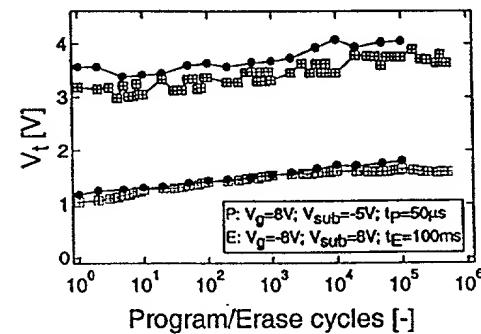


FIG 16 : Endurance characteristic; only limited window closure is observed after 10^5 program/erase cycles.

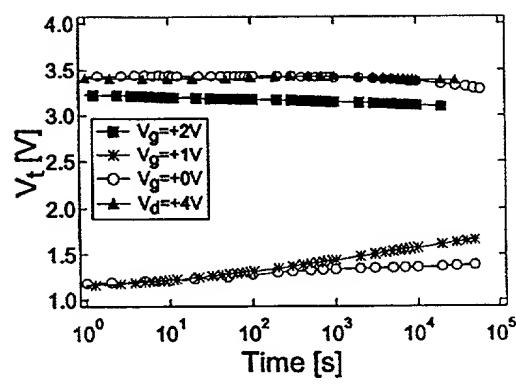


FIGURE 17